NPN SILICON RF POWER TRANSISTOR

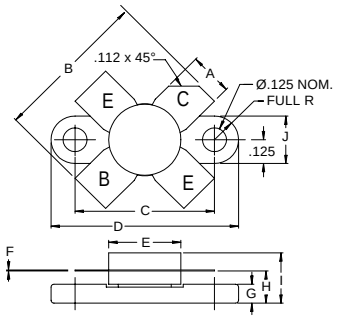
DESCRIPTION:

The **ASI MRF426** is Designed for high gain amplifier applications up to 30 MHz.

FEATURES:

- P_G = 22 dB min. at 25 W/30 MHz
- IMD_3 = -30 dBc max. at 25 W(PEP)
- ***Omnigold***™ Metalization System
- Available as matched pairs.

PACKAGE STYLE .380 4L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.785 / 19.94	
C	.720 / 18.29	.730 / 18.54
D	.970 / 24.64	.980 / 24.89
E		.385 / 9.78
F	.004 / 0.10	.006 / 0.15
G	.085 / 2.16	.105 / 2.67
H	.160 / 4.06	.180 / 4.57
I		.280 / 7.11
J	.240 / 6.10	.255 / 6.48

MAXIMUM RATINGS

I_C	3.0 A
V_{CBO}	65 V
V_{CEO}	35 V
V_{EBO}	4.0 V
P_{DISS}	70 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.5 °C/W

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 50 mA	65			V
BV_{CEO}	I_C = 50 mA	35			V
BV_{EBO}	I_E = 10 mA	4.0			V
I_{CES}	V_{CE} = 28 V			10	mA
h_{FE}	V_{CE} = 5.0 V I_C = 1.0 A	10		200	---
C_{OB}	V_{CB} = 30 V f = 1.0 MHz			80	pF
G_P	V_{CE} = 28 V P_{OUT} = 25 W (PEP) f = 30 MHz	22			dB
η_C		35			%
IMD_3				-30	dBc

FIGURE 2 – OUTPUT POWER versus INPUT POWER

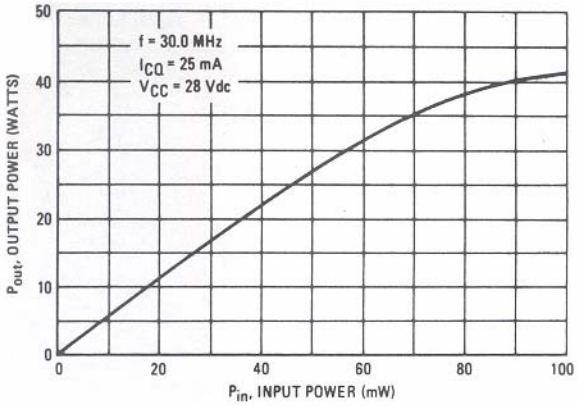


FIGURE 3 – OUTPUT POWER versus SUPPLY VOLTAGE

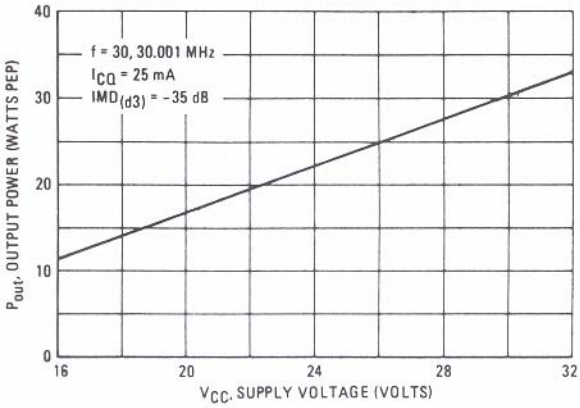


FIGURE 4 – POWER GAIN versus FREQUENCY

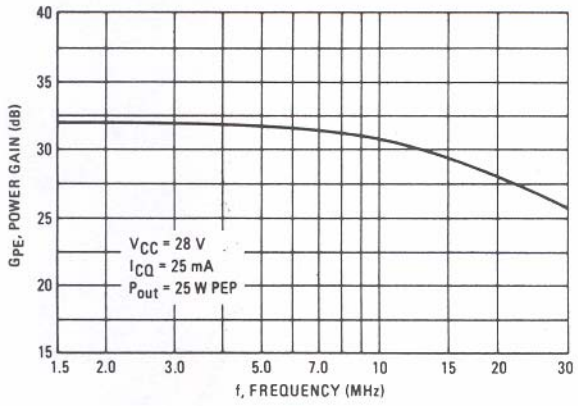


FIGURE 5 – INTERMODULATION DISTORTION versus OUTPUT POWER

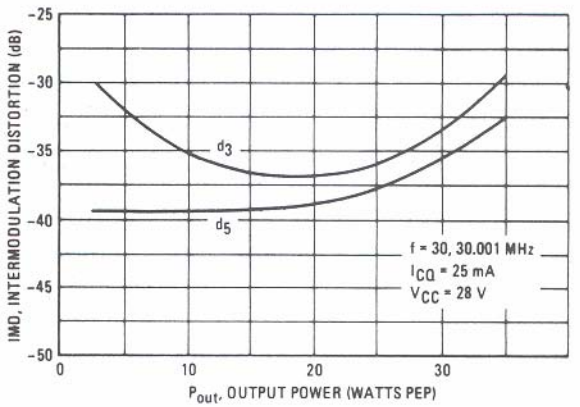


FIGURE 6 – DC SAFE OPERATING AREA